

MOSFET – Power, Single, P-Channel, SC-70

-30 V, -1.3 A

NTS4173P

Features

- -30 V BV_{DS} , Low $R_{DS(on)}$ in SC-70 Package
- Low Threshold Voltage
- Fast Switching Speed
- This is a Halide-Free Device
- This is a Pb-Free Device

Applications

- Load Switch
- Low Current Inverter and DC-DC Converters
- Power Switch for Printers, Communication Equipment

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	−30	V
Gate-to-Source Voltage			V_{GS}	±12	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	−1.2	A
		$T_A = 85\text{ }^{\circ}\text{C}$		−0.80	
	$t \leq 5\text{ s}$	$T_A = 25\text{ }^{\circ}\text{C}$		−1.3	
Power Dissipation (Note 1)	Steady State	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	0.29	W
	$t \leq 5\text{ s}$			0.35	
Pulsed Drain Current	$t_p = 10\text{ }\mu\text{s}$		I_{DM}	−5.0	A
Operating Junction and Storage Temperature			T_J , T_{stg}	−55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	−1.0	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

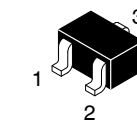
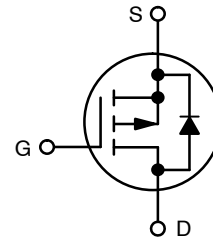
THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	425	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 5\text{ s}$ (Note 1)	$R_{\theta JA}$	360	

1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)

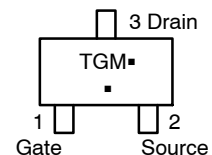
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
-30 V	150 m Ω @ -10 V	-1.2 A
	200 m Ω @ -4.5 V	-1.0 A
	280 m Ω @ -2.5 V	-0.9 A

SC-70/SOT-323 (3 LEADS)



SC-70 (SOT-323)
CASE 419
STYLE 8

MARKING DIAGRAM/ PIN ASSIGNMENT



TG = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

* Date code orientation may vary depending upon manufacturing location

ORDERING INFORMATION

Device	Package	Shipping [†]
NTS4173PT1G	SC-70 (SOT-323) (Pb-Free)	3000/ Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).

NTS4173P

MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}, T_J = 25\text{ }^{\circ}\text{C}$ $V_{GS} = 0\text{ V}, V_{DS} = -24\text{ V}, T_J = 85\text{ }^{\circ}\text{C}$			-1.0 -5.0	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 0.1	μA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-0.7	-1.15	-1.5	V
Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -1.2\text{ A}$		90	150	$\text{m}\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -1.0\text{ A}$		110	200	
		$V_{GS} = -2.5\text{ V}, I_D = -0.9\text{ A}$		165	280	
Forward Transconductance	g_{FS}	$V_{DS} = -5\text{ V}, I_D = -1.2\text{ A}$		3.6		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz},$ $V_{DS} = -15\text{ V}$		430		pF
Output Capacitance	C_{oss}			55		
Reverse Transfer Capacitance	C_{rss}			40		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V},$ $I_D = -1.2\text{ A}$		4.8		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.6		
Gate-to-Source Charge	Q_{GS}			1.1		
Gate-to-Drain Charge	Q_{GD}	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V},$ $I_D = -1.2\text{ A}$		1.5		nC
Total Gate Charge	$Q_{G(TOT)}$			10.1		
Threshold Gate Charge	$Q_{G(TH)}$			0.6		
Gate-to-Source Charge	Q_{GS}			1.1		
Gate-to-Drain Charge	Q_{GD}			1.5		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -15\text{ V},$ $I_D = -1.2\text{ A}, R_G = 3\text{ }\Omega$		7.7		ns
Rise Time	t_r			5.2		
Turn-Off Delay Time	$t_{d(off)}$			16.2		
Fall Time	t_f			6.7		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V},$ $I_D = -1.2\text{ A}, R_G = 3\text{ }\Omega$		5.3		ns
Rise Time	t_r			6.7		
Turn-Off Delay Time	$t_{d(off)}$			19.9		
Fall Time	t_f			7.1		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -1.0\text{ A}$		-0.8	-1.0	V
Reverse Recovery Time	t_{RR}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, I_S = -1.0\text{ A},$ $dI_{SD}/dt = 100\text{ A}/\mu\text{s}$		12		ns
Charge Time	t_a			10		
Discharge Time	t_b			2.0		
Reverse Recovery Charge	Q_{RR}			7.0		nC

2. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces)
3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2\%$
4. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

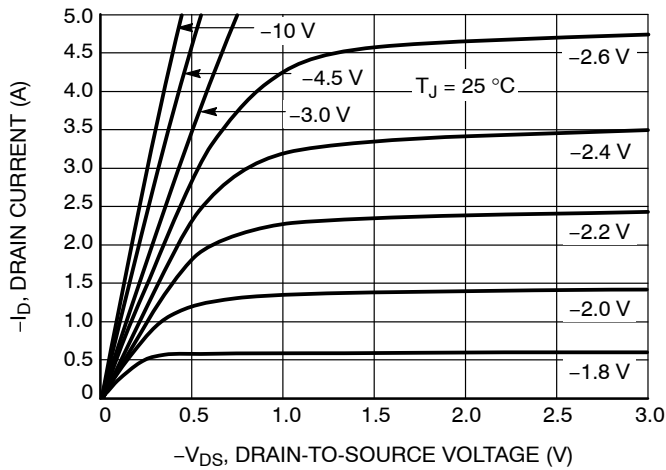


Figure 1. On-Region Characteristics

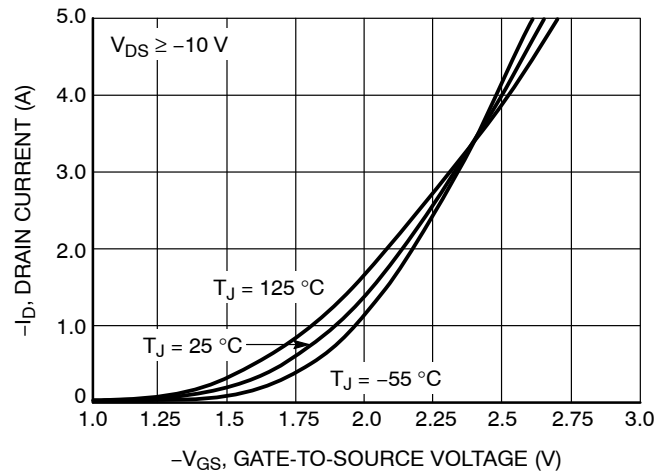


Figure 2. Transfer Characteristics

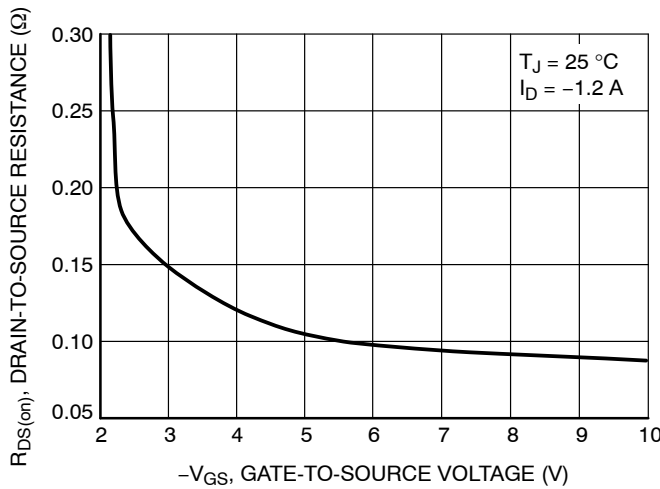


Figure 3. On-Resistance vs. Gate Voltage

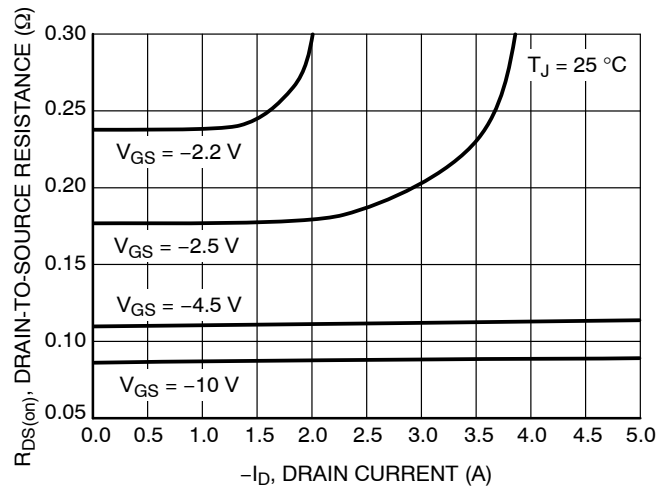


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

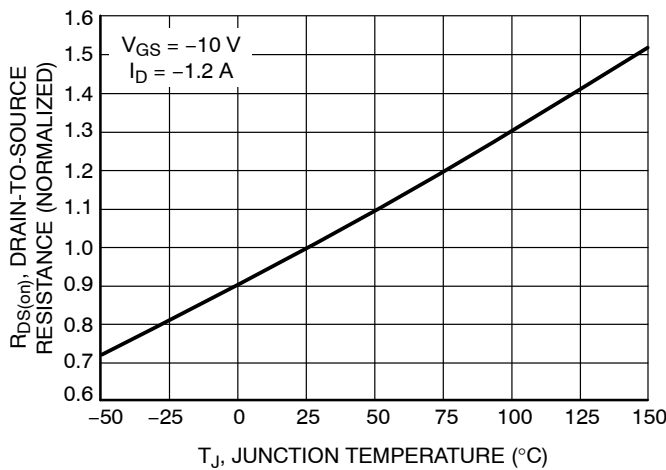


Figure 5. On-Resistance Variation with Temperature

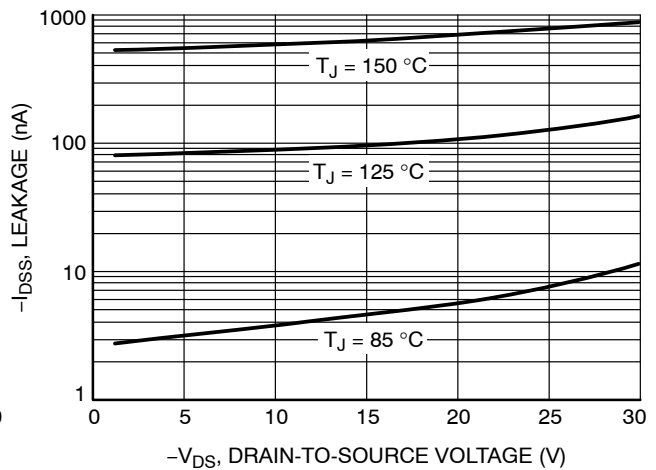


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

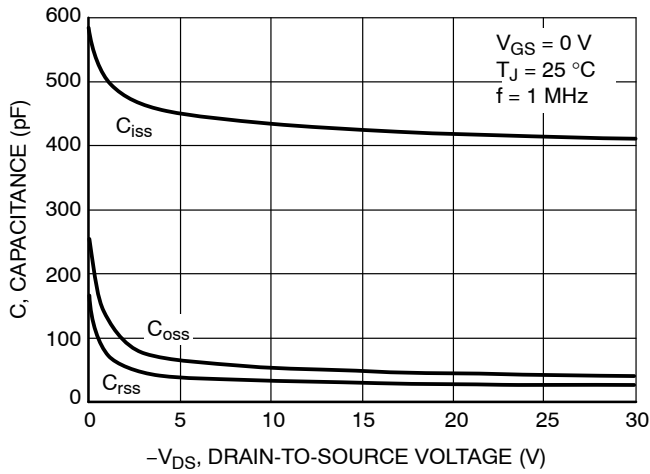


Figure 7. Capacitance Variation

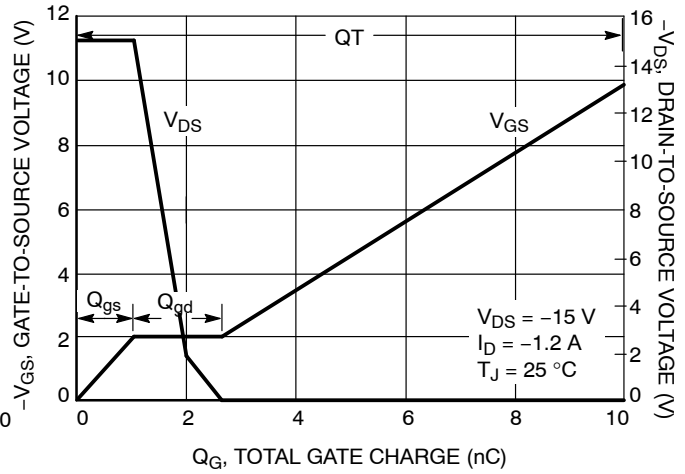


Figure 8. Gate-to-Source Voltage vs. Total Charge

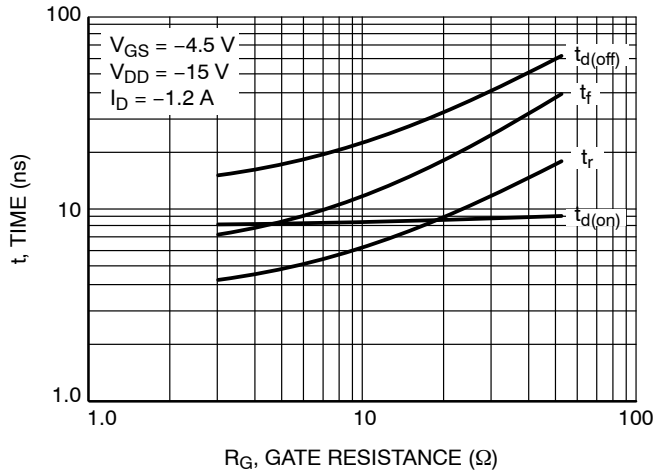


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

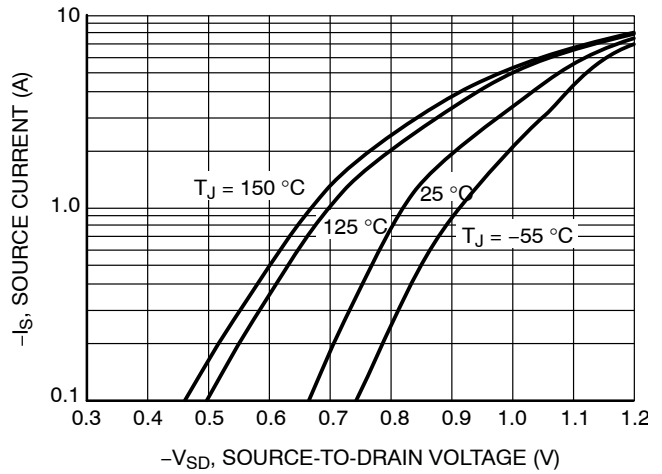


Figure 10. Diode Forward Voltage vs. Current

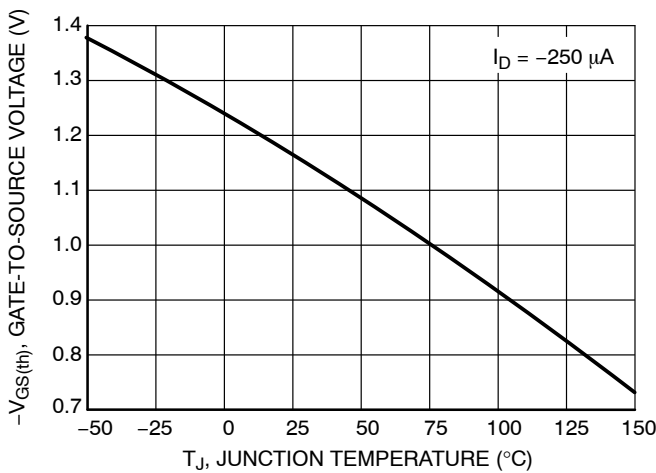


Figure 11. Threshold Voltage

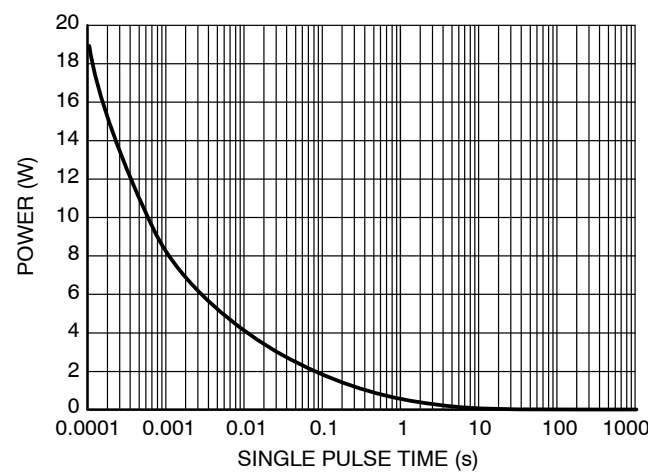


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL PERFORMANCE CURVES

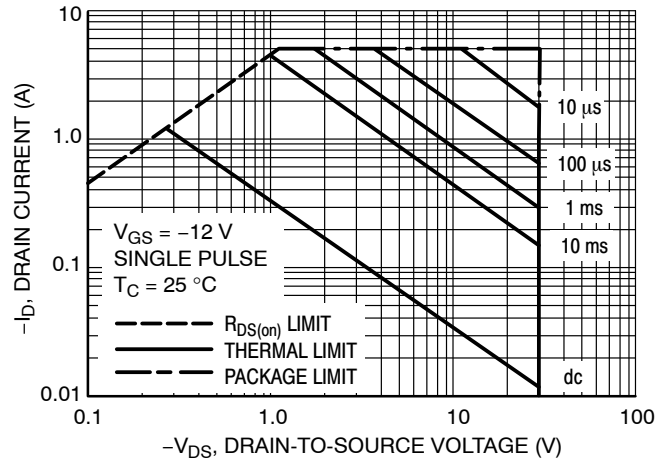


Figure 13. Maximum Rated Forward Biased Safe Operating Area

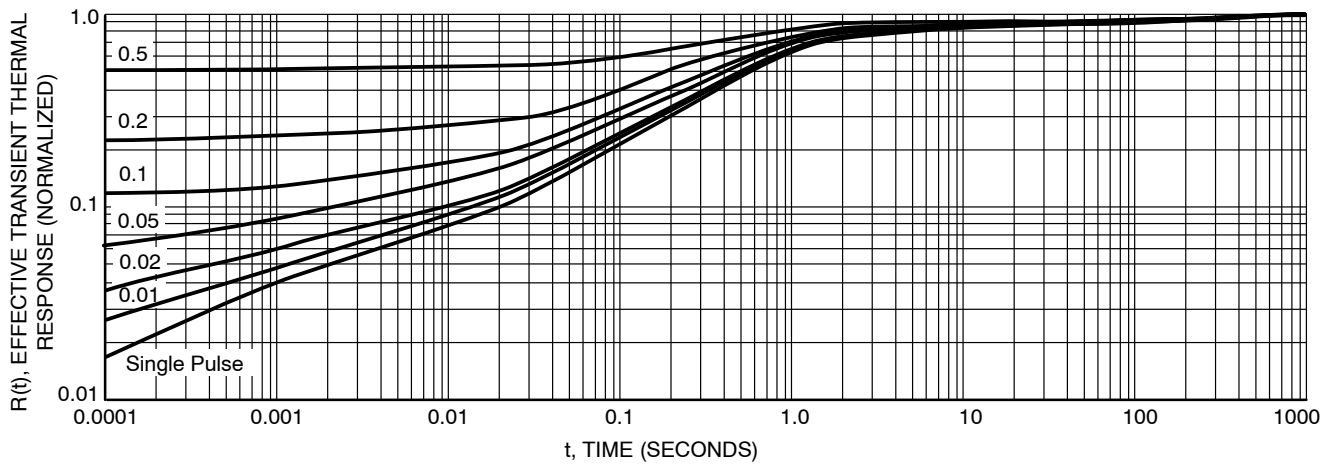


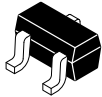
Figure 14. FET Thermal Response

NTS4173P

REVISION HISTORY

Revision	Description of Changes	Date
0	Initial production document version release.	6/16/2019
1	Document rebranded to onsemi format.	1/28/2026

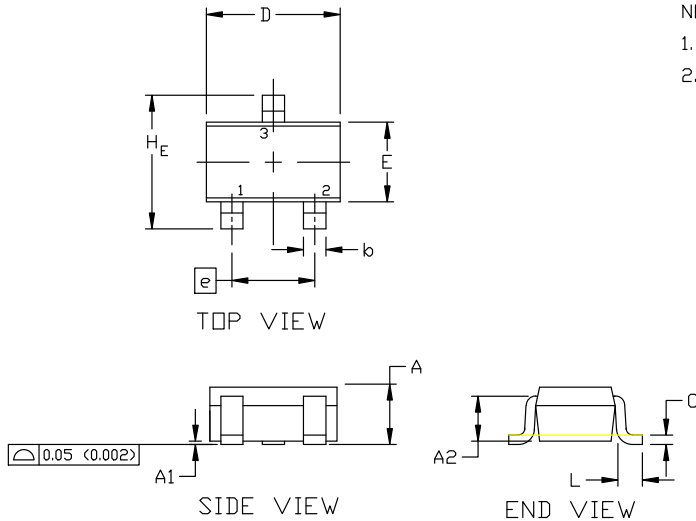




SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE R

DATE 11 OCT 2022

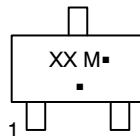


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

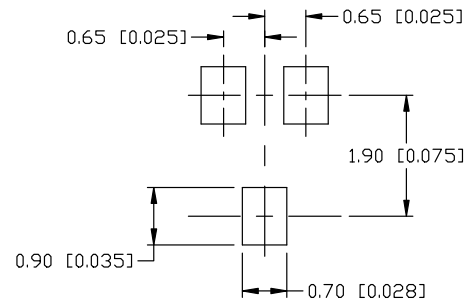
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC
MARKING DIAGRAM



XX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:
CANCELLED

STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE

STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE

STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

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